

DERWENT-ACC-NO: 2002-252539
DERWENT-WEEK: 200230
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TITLE: Method for forming dielectric layer with capability to resist the diffusion of copper effectively increases the capability to resist the diffusion of copper for the material with a low dielectric constant

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PATENT-ASSIGNEE: UNITED MICROELECTRONICS CORP[UNMIN]

PRIORITY-DATA: 1999TW-0122132 (December 16, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 429473 A	April 11, 2001	N/A	000	H01L 021/31

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
TW 429473A	N/A	1999TW-0122132	December 16, 1999

INT-CL (IPC): H01L021/31

ABSTRACTED-PUB-NO: TW 429473A

BASIC-ABSTRACT: NOVELTY - A method for forming dielectric layer with a capability to resist the diffusion of copper comprises the steps of: first, providing a substrate and then performing a spin-on step to form a dielectric layer with a low dielectric constant on the substrate; then, sequentially performing a baking step and a curing step; and finally, performing a plasma processing step to the dielectric layer.

CHOSEN-DRAWING: Dwg.1/1

TITLE-TERMS:

METHOD FORMING DIELECTRIC LAYER CAPABLE RESIST DIFFUSION
COPPER EFFECT INCREASE
CAPABLE RESIST DIFFUSION COPPER MATERIAL LOW DIELECTRIC
CONSTANT

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